

SS5817D THRU SS5819D

SURFACE MOUNT SCHOTTKY BARRIER RECTIFIERS

Reverse Voltage - 20 to 40 V

Forward Current - 1 A

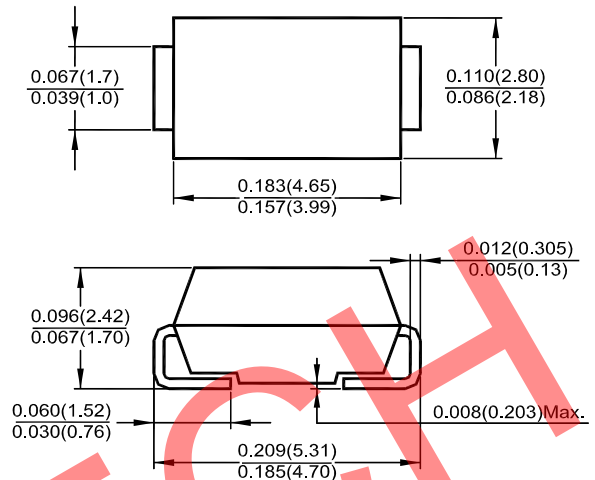
Features

- Plastic package has Underwriters Laboratory Classification 94V-0
- Metal silicon junction, majority carrier conduction
- For surface mount applications
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, Low forward voltage drop
- High surge capability

Mechanical Data

- **Case:** SMA (DO-214AC) molded plastic case
- **Terminals:** Solder plate, solderable per MIL-STD -750, method 2026
- **Polarity:** Color band denotes cathode end
- **Mounting Position:** Any

SMA (DO-214AC)



Dimensions in inches and (millimeters)

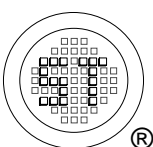
Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	SS5817D	SS5818D	SS5819D	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS Voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current 0.375" (9.5 mm) Load Length at $T_L = 90^\circ\text{C}$	$I_{F(AV)}$	1			A
Peak Forward Surge Current 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) at $T_L = 70^\circ\text{C}$	I_{FSM}	25			A
Maximum Instantaneous Forward Voltage at 1 A	V_F	0.45	0.55	0.6	V
Maximum Instantaneous Reverse Current at Rated DC Blocking Voltage at $T_a = 25^\circ\text{C}$ at $T_a = 100^\circ\text{C}$	I_R	0.5 10			mA
Typical Junction Capacitance ¹⁾	C_j	110			pF
Typical Thermal Resistance ²⁾	$R_{\theta JA}$	88			°C/W
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125			°C

¹⁾ Measured at 1 MHz and reverse voltage of 4 V.

²⁾ Thermal Resistance (from Junction to Ambient) Vertical P.C.B Mounted, with 1.5 X 1.5" (38 X 38 mm) copper pads.



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FIG.1-FORWARD CURRENT DERATING CURVE

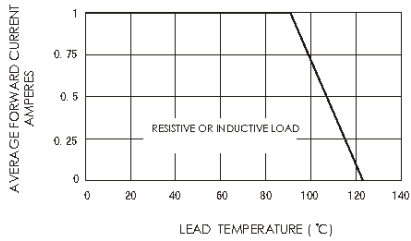


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

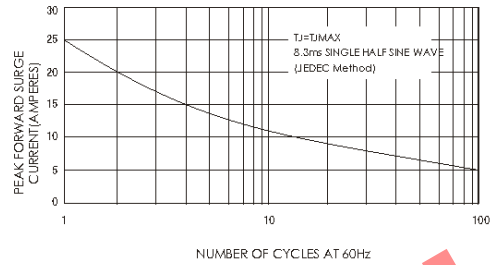


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

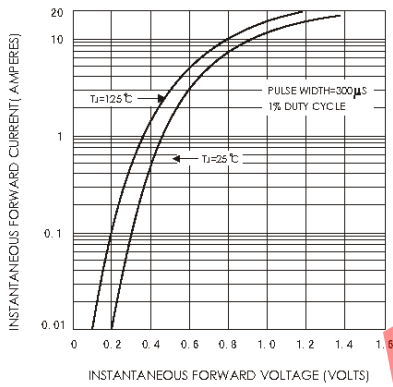


FIG.4-TYPICAL REVERSE CHARACTERISTICS

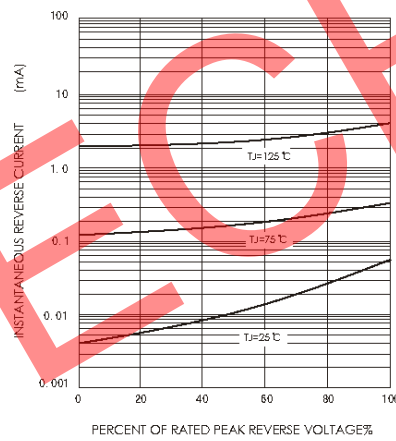


FIG.5-TYPICAL JUNCTION CAPACITANCE

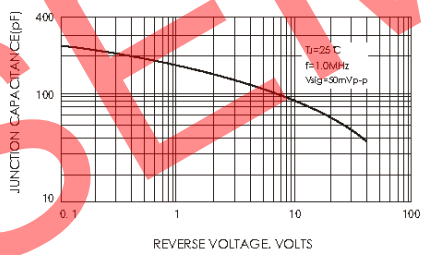
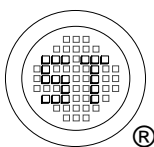
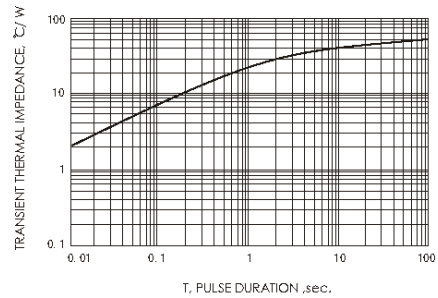


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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